IN THE CLAIMS

1 (Currently Amended. An integrated memory system, comprising:

at least a non-volatile solid-state memory; and

an automatic storage error corrector, characterized in that the memory system comprises circuit means, including functionally independent, each of them being responsible for the correction of a devices, each device to correct a different predetermined storage error of data stored in the memory,[[;]] at least one of said means generating a signal to ask a correction devices being external to the memory.

2 (Currently Amended). A system according to claim 1, wherein characterized in that said memory is connected to a controller by means of an interface bus and said devices circuit means are incorporated both in the memory and in the controller.

3 (Currently Amended). A system according to claim 1, <u>including characterized in</u> that, in the memory, said means comprise: <u>coding circuits to correct two errors</u>, a <u>logic to calculate</u> a <u>syndrome</u>, a <u>single error correcting circuit</u>, and a <u>logic to detect more than one error</u>.

circuits for the coding required to correct two errors;

a logic for calculating a syndrome;

circuit-for correcting a single error;

a logic for detecting more than one error.

4 (Currently Amended). A system according to claim 3, <u>further including</u> characterized in that said means also comprise: <u>a logic to supply the controller with a one-or-no-error-corrected data</u>, the uncorrected error, and the calculated syndrome.

a logic for bringing to the controller:

a one-or-no-error-corrected data;

the uncorrected-error; and

the calculated syndrome.

- 5 (Currently Amended). A system according to claim 2, <u>including eharacterized in</u> that said circuit means comprise a circuit to generate for generating a signal activated to request the external correction of an error by said controller.
- 6 (Currently Amended). A system according to claim 3, wherein characterized in that said coding circuits are located immediately downstream of the input terminal of said memory to and perform a vector product proportional to the number of parity bits and obtained through the synthesis of a corresponding logic function.
- 7 (Currently Amended). A system according to claim 6, wherein characterized in that said logic to calculate for calculating the syndrome to use uses a parity calculation circuit of the coding circuits.
- 8 (Currently Amended). A system according to claim 3, wherein characterized in that said single error correcting circuit for correcting a single an error comprises a block to decode for decoding a single error effective to recognize recognise each of the several syndromes associated to a single error to activate, through a corresponding vector, the correction of the corresponding bit.

9 (Previously Presented). A system, comprising:

- a first circuit operable to store data in a non-volatile solid-state memory, the data having associated therewith at least one storage error of a plurality of storage-error types, the first circuit operable to correct a first-type error of the plurality of storage-error types; and
- a second circuit coupled to the first circuit, the second circuit operable to correct a second-type error of the plurality of storage-error types.
- 10 (Currently Amended). The system of claim 9 wherein the second circuit is operable to generate a signal requesting correction of a third-type error of the plurality of storage-error types.

- 11 (Currently Amended). The system of claim 9 wherein the first circuit [[is]] further operable to determine at least one syndrome associated with the at least one storage error.
- 12 (Currently Amended). The system of claim 9 wherein the first circuit [[is]] further operable to detect the second-type error.
- 13 (Currently Amended). The system of claim 9 wherein the second circuit to correct corrects the second-type error in response to a signal generated by the first circuit.
- 14 (Original). The system of claim 9 wherein the first circuit comprises a non-volatile memory.
 - 15 (Original). The system of claim 9 wherein:
 the first circuit is disposed on a first integrated circuit; and
 the second circuit is disposed on a second integrated circuit.
- 16 (Original). The system of claim 9 wherein the first and second circuits are disposed on an integrated circuit.
 - 17 (Currently Amended). A memory device, comprising:
- a non-volatile solid-state storage portion operable to store data having associated therewith at least one storage error of a plurality of storage-error types;
- a first circuit operable to correct a first-type error of the plurality of storage-error types; and
- a second circuit operable to generate a signal indicating detection of a second-type error of the plurality of storage-error types.
- 18 (Currently Amended). The device of claim 17, further comprising a third circuit operable to determine at least one syndrome associated with the at least one storage error.

19 (Previously Presented). A method, comprising:

storing, in a non-volatile solid-state memory location of a device, data having associated therewith at least one storage error of a plurality of storage-error types; and correcting, at the memory location, a first-type error of the plurality of storage-error types.

20 (Original). The method of claim 19, further comprising generating, at the memory location, an interrupt-request signal indicating detection of a second-type error of the plurality of storage-error types.

21 (Currently Amended). An electronic system, comprising:

a first integrated circuit having a non-volatile solid-state memory operable to store data having associated therewith at least one storage error of a plurality of storage-error types, the memory operable to correct a first-type error of the plurality of storage-error types; and

a second integrated circuit coupled to the first circuit, the second integrated circuit having processor operable to correct a second-type error of the plurality of storage-error types.